



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

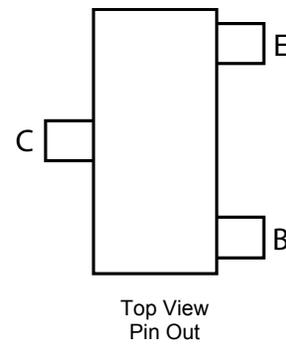
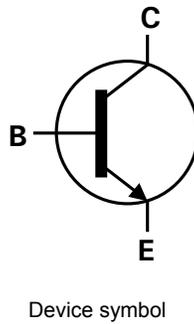
- 3.2GHz unity gain for RF switching applications

Applications

- RF Switch

Mechanical Data

- Case: SOT323
- Case Material: molded plastic, "Green" molding compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 [Ⓔ]3
- Weight: 0.006 grams (approximate)



Maximum Ratings (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	11	V
Emitter-Base Voltage	V_{EBO}	3	V
Continuous Collector Current	I_C	50	mA

Thermal Characteristics (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

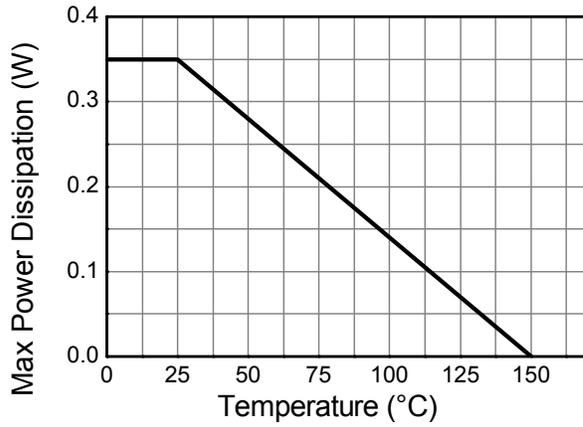
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	(Note 5) 310	mW
		(Note 6) 350	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	(Note 5) 403	$^{\circ}\text{C}/\text{W}$
		(Note 6) 357	
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	350	$^{\circ}\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^{\circ}\text{C}$

ESD Ratings (Note 8)

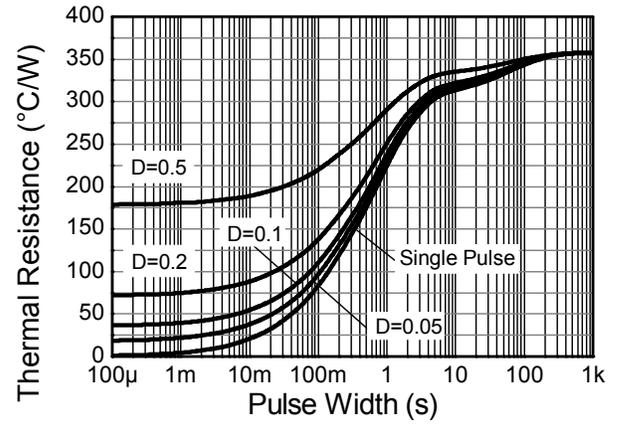
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	100	V	A

- Notes:
5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition;
 6. Same as Note 6, expect the device is mounted on 15mm X 15mm X 1.6mm FR4 PCB
 7. Thermal resistance from junction to solder-point (at the end of the leads).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

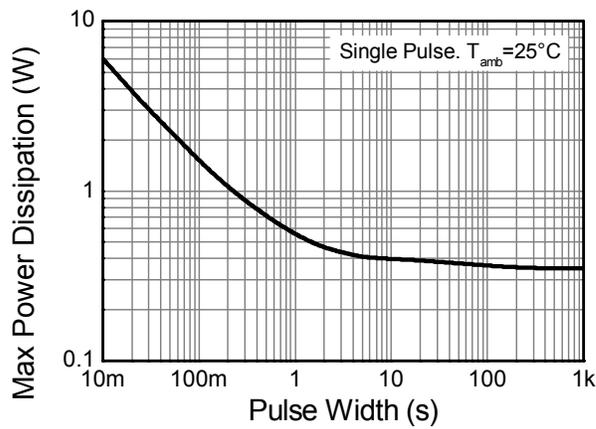
Thermal Characteristics and Derating information



Derating Curve



Transient Thermal Impedance



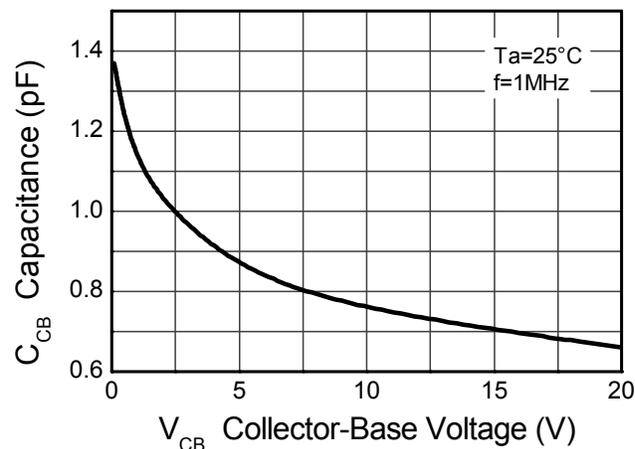
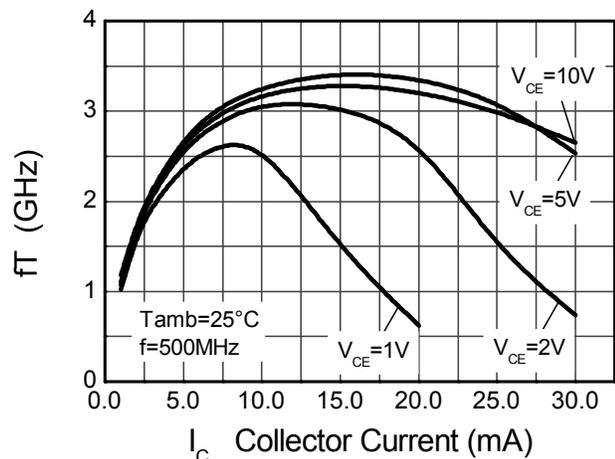
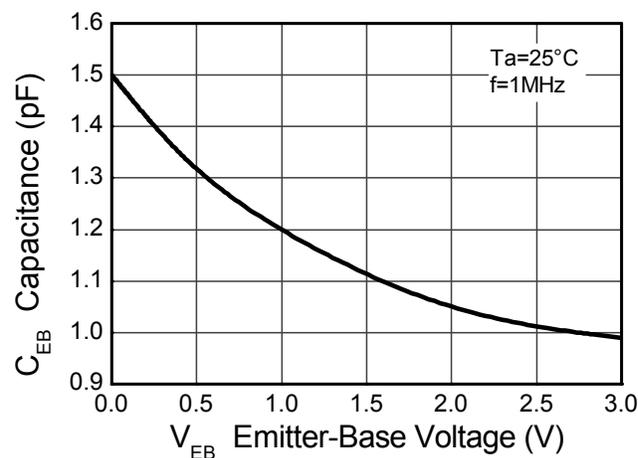
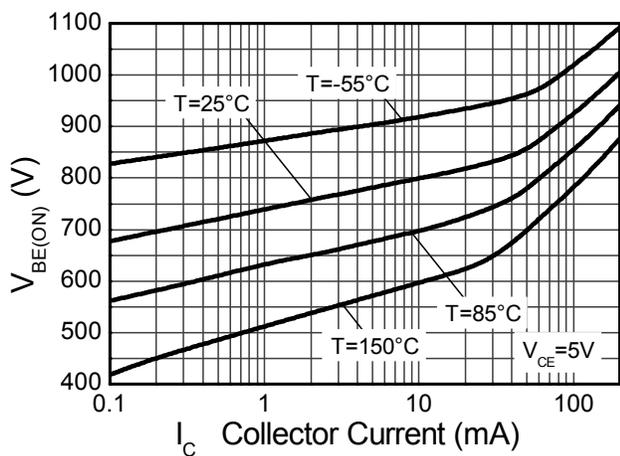
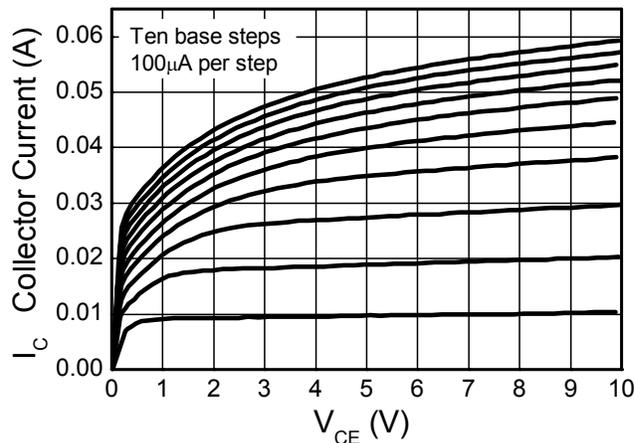
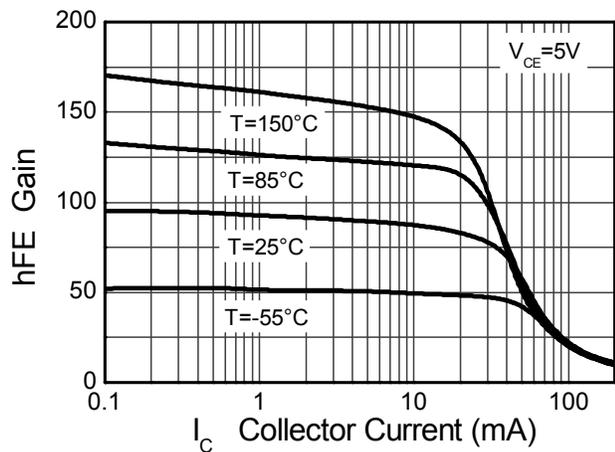
Pulse Power Dissipation

Electrical Characteristics (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

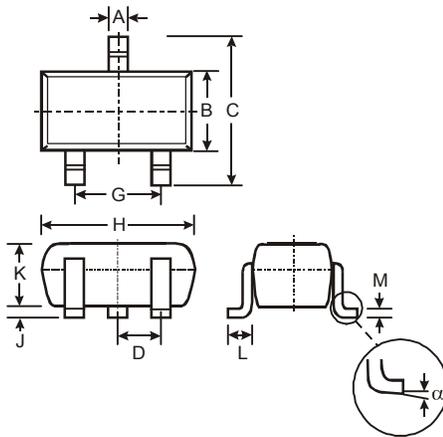
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	20	—	—	V	$I_C = 10\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	11	—	—	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	3	—	—	V	$I_E = 10\mu\text{A}$
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	$V_{CE} = 10\text{V}$
Emitter Cutoff Current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 2\text{V}$
Static Forward Current Transfer Ratio (Note 9)	h_{FE}	56	—	180	—	$I_C = 5\text{mA}$, $V_{CE} = 10\text{V}$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(SAT)}$	—	—	0.5	V	$I_C = 10\text{mA}$, $I_B = 5\text{mA}$
Transition Frequency (Note 9)	f_T	1.4	3.2	—	GHz	$V_{CE} = 5\text{V}$, $I_E = 25\text{mA}$, $f = 500\text{MHz}$
Collector Output Capacitance (Note 9)	C_{ob}	—	0.8	1.5	pF	$V_{CB} = 10\text{V}$, $f = 1.0\text{MHz}$

 Notes: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

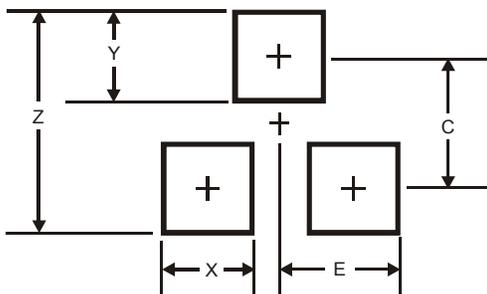


Package Outline Dimensions



SOT323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0